NJ450L Process

Silicon Junction Field-Effect Transistor

- Low-Current
- Low Gate Leakage Current
- High Input Impedance

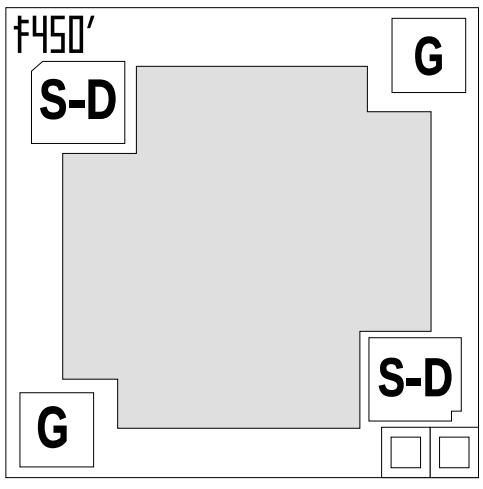
Absolute maximum ratings at 25°C free-air temperature.

Gate Current, Ig	10 mA
Operating Junction Temperature, Tj	+150°C
Storage Temperature, Ts	– 65°C to +175°C

Devices in this Databook based on the NJ450L Process.

Datasheet

2N6550
IF4500
IF4501
IFN860



Die Size = 0.028" X 0.028"
All Bond Pads = 0.004" Sq.
Substrate is also Gate.

At 25°C free air temperature: Static Electrical Characteristics		NJ450L Process Min	Typ	Max	Unit	Test Conditions	
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	– 25	– 25		V	I_G = – 1 µA, V_{DS} = ØV	
Reverse Gate Leakage Current	I_{GSS}		– 50		pA	V_{GS} = – 15V, V_{DS} = ØV	
Drain Saturation Current (Pulsed)	I_{DSS}	5			mA	V_{DS} = 15V, V_{GS} = ØV	
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	– 0.1		– 4	V	V_{DS} = 15V, I_D = 1 nA	
Dynamic Electrical Characteristics							
Forward Transconductance (Pulsed)	g_{fs}		100		mS	V_{DS} = 15V, V_{GS} = ØV	f = 1 kHz
Input Capacitance	C_{iss}		35		pF	V_{DS} = ØV, V_{GS} = – 10V	f = 1 MHz
Feedback Capacitance	C_{rss}		10		pF	V_{DS} = ØV, V_{GS} = – 10V	f = 1 MHz
Equivalent Noise Voltage	$\bar{e}_N$		0.9		nV/√HZ	V_{DG} = 4V, I_D = 5 mA	f = 1 kHz

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